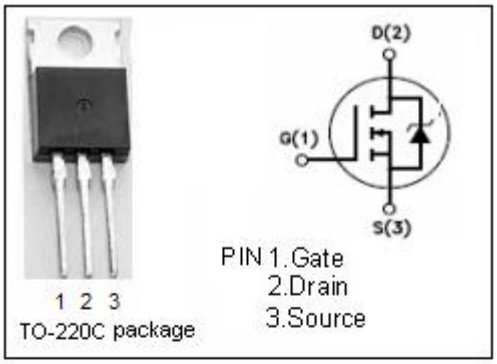
isc N-Channel MOSFET Transistor 2SK1707

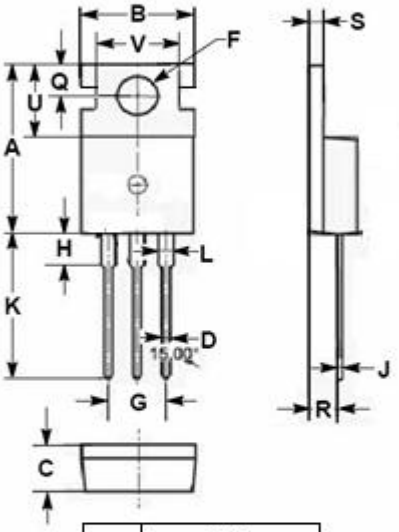


DESCRIPTION

- Drain Current –I_D= 4A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= 600V(Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power supplies, converters and power motor controls



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	600	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ TC=25℃	4	A
P_{tot}	Total Dissipation@TC=25℃	90	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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• ELECTRICAL CHARACTERISTICS (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= 1mA	600		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D=1mA	2.0	4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 2A		2.6	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±30V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= 600V; V_{GS}= 0		1	mA